**Vishay Semiconductors** 



RoHS

COMPLIANT

# Silicon NPN Phototransistor, RoHS Compliant



## DESCRIPTION

BPV11F is a silicon NPN phototransistor with high radiant sensitivity in black, T-1¾ plastic package with base terminal and daylight blocking filter. Filter bandwidth is matched with 900 nm to 950 nm IR emitters.

# FEATURES

- Package type: leaded
- Package form: T-1¾
- Dimensions (in mm): Ø 5
- High radiant sensitivity
- Daylight blocking filter matched with 940 nm emitters
- Fast response times
- Angle of half sensitivity:  $\phi = \pm 15^{\circ}$
- Base terminal connected
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

## APPLICATIONS

• Detector for industrial electronic circuitry, measurement and control

# PRODUCT SUMMARY

COMPONENT	I <sub>ca</sub> (mA)	φ <b>(deg)</b>	λ <sub>0.5</sub> (nm)
BPV11F	9	± 15	900 to 980

#### Note

Test condition see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
BPV11F	Bulk	MOQ: 3000 pcs, 3000 pcs/bulk	T-1¾	
BPVIIF	BUIK	NOQ: 3000 pcs, 3000 pcs/bulk	1-1%	

### Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector base voltage		V <sub>CBO</sub>	80	V
Collector emitter voltage		V <sub>CEO</sub>	70	V
Emitter base voltage		V <sub>EBO</sub>	5	V
Collector current		Ι <sub>C</sub>	50	mA
Collector peak current	$t_p/T=0.5,t_p\leq 10\ ms$	I <sub>CM</sub>	100	mA
Power dissipation	$T_{amb} \le 47 \ ^{\circ}C$	Pv	150	mW
Junction temperature		Tj	100	°C
Operating temperature range		T <sub>amb</sub>	- 40 to + 100	°C
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C
Soldering temperature	$t \le 5 s$ , 2 mm from body	T <sub>sd</sub>	260	°C
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm <sup>2</sup>	R <sub>thJA</sub>	350	K/W

#### Note

T<sub>amb</sub> = 25 °C, unless otherwise specified



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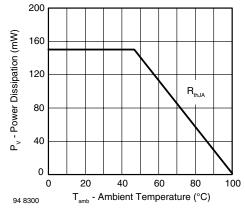


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	I <sub>C</sub> = 1 mA	V <sub>(BR)CEO</sub>	70			V
Collector emitter dark current	V <sub>CE</sub> = 10 V, E = 0	I <sub>CEO</sub>		1	50	nA
DC current gain	$V_{CE} = 5 V, I_C = 5 mA, E = 0$	h <sub>FE</sub>		450		
Collector emitter capacitance	V <sub>CE</sub> = 0 V, f = 1 MHz, E = 0	C <sub>CEO</sub>		15		pF
Collector base capacitance	V <sub>CE</sub> = 0 V, f = 1 MHz, E = 0	C <sub>CBO</sub>		19		pF
Collector light current	$\begin{array}{l} E_{e} = 1 \ mW/cm^2,  \lambda = 950 \ nm, \\ V_{CB} = 5 \ V \end{array}$	I <sub>ca</sub>	3	9		mA
Angle of half sensitivity		φ		± 15		deg
Wavelength of peak sensitivity		λρ		930		nm
Range of spectral bandwidth		λ <sub>0.5</sub>		900 to 980		nm
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, \\ I_C = 1 \text{ mA}$	V <sub>CEsat</sub>		130	300	mV
Turn-on time	$V_{S}$ = 5 V, $I_{C}$ = 5 mA, $R_{L}$ = 100 $\Omega$	t <sub>on</sub>		6		μs
Turn-off time	$V_{S}$ = 5 V, $I_{C}$ = 5 mA, $R_{L}$ = 100 $\Omega$	t <sub>off</sub>		5		μs
Cut-off frequency	$V_{S} = 5 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ R}_{L} = 100 \Omega$	f <sub>c</sub>		110		kHz

#### Note

 $T_{amb}$  = 25 °C, unless otherwise specified

## **BASIC CHARACTERISTICS**

 $T_{amb}$  = 25 °C, unless otherwise specified

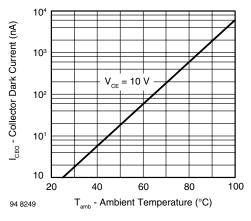


Fig. 2 - Collector Dark Current vs. Ambient Temperature

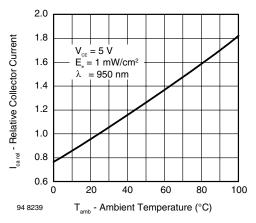


Fig. 3 - Relative Collector Current vs. Ambient Temperature

For technical questions, contact: detectortechsupport@vishay.com

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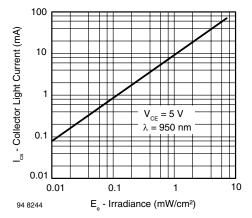


Fig. 4 - Collector Light Current vs. Irradiance

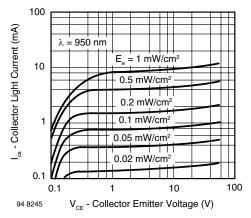


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

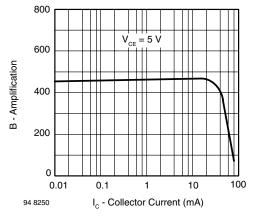


Fig. 6 - Amplification vs. Collector Current

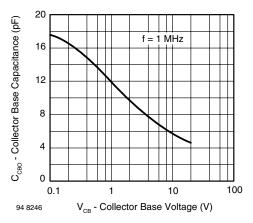


Fig. 7 - Collector Base Capacitance vs. Collector Base Voltage

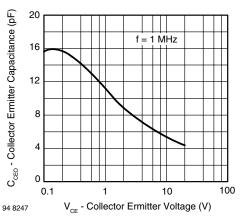


Fig. 8 - Collector Emitter Capacitance vs. Collector Emitter Voltage

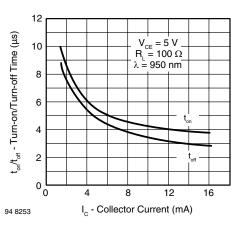


Fig. 9 - Turn-on/Turn-off Time vs. Collector Current



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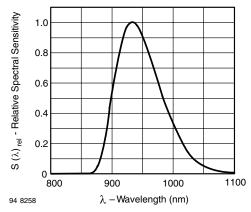


Fig. 10 - Relative Spectral Sensitivity vs. Wavelength

### **PACKAGE DIMENSIONS** in millimeters

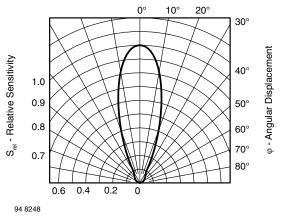
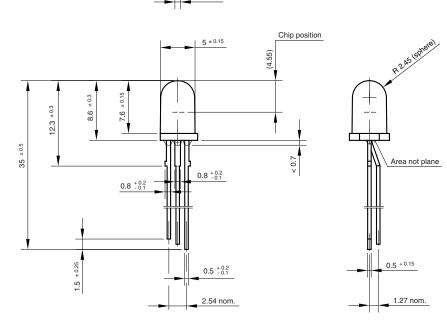


Fig. 11 - Relative Radiant Sensitivity vs. Angular Displacement



5.75 ±0.15

С

В

0.8 + 0.2

Е



technical drawings according to DIN specifications

Drawing-No.: 6.544-5188.01-4 Issue:1; 01.07.96 96 12200



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